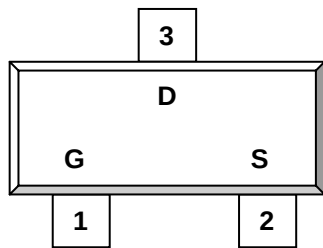


DESCRIPTION

The ST7407 is the P-Channel logic enhancement mode power field effect transistors It is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone, notebook computer power management and other battery powered circuits where high-side switching, and low in-line power loss are needed in a very small outline surface mount package.

PIN CONFIGURATION SOT-323 (SC-70)

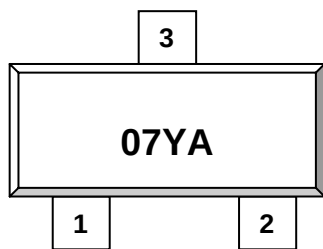


1.Gate 2.Source 3.Drain

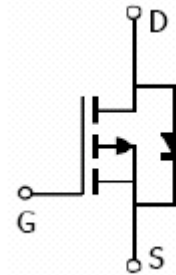
FEATURE

- -20V/-3.4A, $R_{DS(ON)} = 100\text{m-ohm}$ @VGS = -4.5V
- -20V/-2.4A, $R_{DS(ON)} = 125\text{m-ohm}$ @VGS = -2.5V
- -20V/-1.8A, $R_{DS(ON)} = 170\text{m-ohm}$ @VGS = -1.8V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-323 (SC-70) package design

PART MARKING SOT-323 (SC-70)



Y: Year Code A: Process Code



ORDERING INFORMATION

Part Number	Package	Part Marking
ST7407S32RG	SOT-323	07YA

※ Process Code : A ~ Z ; a ~ z

※ ST7407S32RG S32 : SOT-323 ; R : Tape Reel ; G : Pb – Free



ST7407 

P Channel Enhancement Mode MOSFET

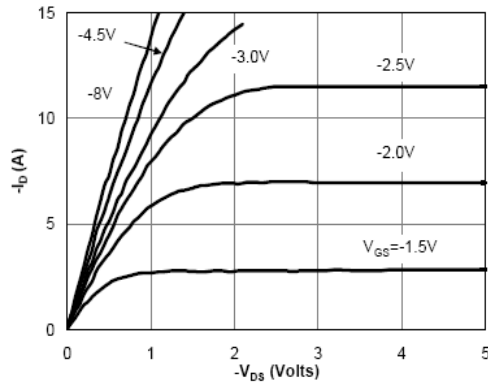
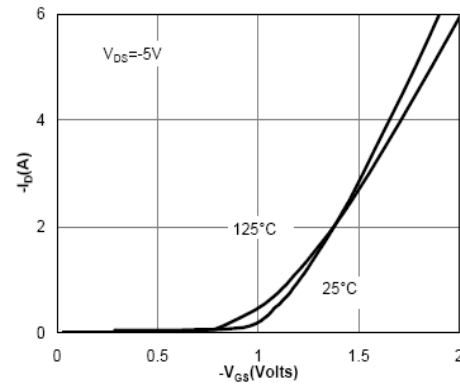
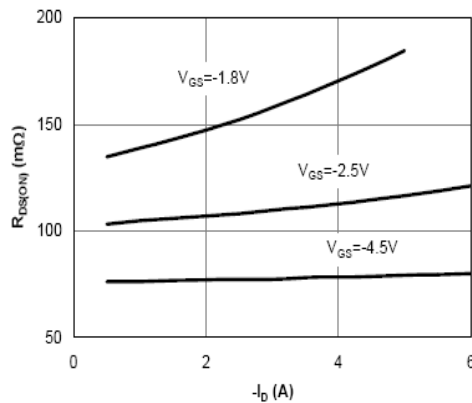
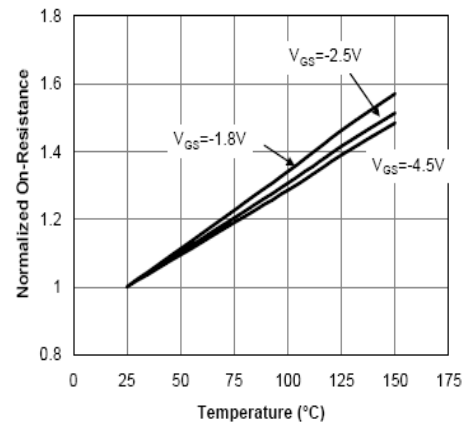
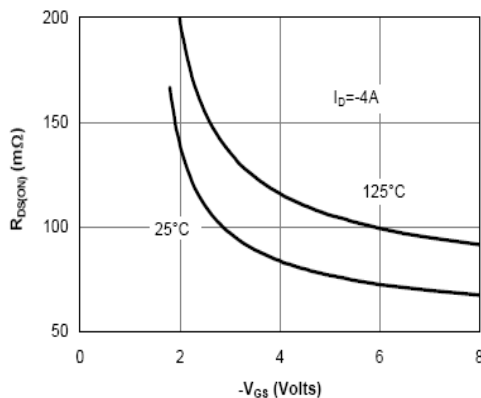
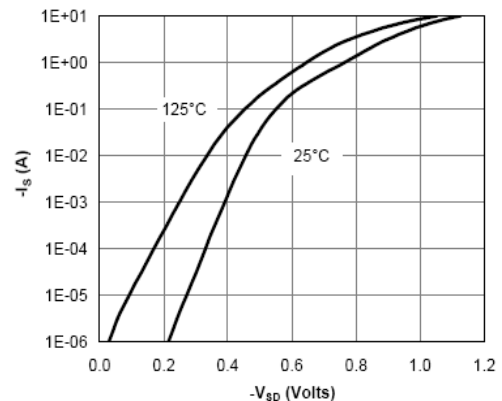
-3.4A

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V _{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±12	V
Continuous Drain Current (T _J = 150°C)	T _A = 25°C T _A = 70°C	I _D	-2.3 -1.7	A
Pulsed Drain Current		I _{DM}	-6	A
Continuous Source Current (Diode Conduction)		I _S	-1.4	A
Power Dissipation	T _A = 25°C T _A = 70°C	P _D	0.35 0.22	W
Operation Junction Temperature		T _J	150	°C
Storage Temperature Range		T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient		R _{θJA}	120	°C/W

ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D = -250uA	-20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = -250uA	-0.35		-0.8	V
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V, V _{GS} =0V			-1	uA
		V _{DS} = -20V, V _{GS} =0V T _J =55℃			-5.0	
On-State Drain Current	I _{D(on)}	V _{DS} ≤ -5V, V _{GS} = -4.5V V _{DS} ≤ -5V, V _{GS} = -2.5V	-6 -3			A
Drain-source On-Resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -3.4A V _{GS} = -2.5V, I _D = -2.4A V _{GS} = -1.8V, I _D = -1.8A		0.090 0.115 0.150	0.100 0.125 0.170	Ω
Forward Transconductance	g _{fs}	V _{DS} = -5V, I _D = -2.8V		6.0		S
Diode Forward Voltage	V _{SD}	I _S = -1.6A, V _{GS} =0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} = -6V V _{GS} = -4.5V I _D ≡ -2.8A		4.8	8.0	nC
Gate-Source Charge	Q _{gs}			1.0		
Gate-Drain Charge	Q _{gd}			1.0		
Input Capacitance	C _{iss}	V _{DS} = -6.0V V _{GS} =0V F=1MHz		485		pF
Output Capacitance	C _{oss}			85		
Reverse Transfer Capacitance	C _{rss}			40		
Turn-On Time	t _{d(on)} tr	V _{DD} = -6V R _L =6Ω I _D = -1.0A V _{GEN} = -4.5V R _G =6Ω		10	16	nS
				13	23	
Turn-Off Time	t _{d(off)} tf			18	25	
				15	20	

TYPICAL CHARACTERISTICS (25°C Unless noted)

Fig 1: On-Region Characteristics

Figure 2: Transfer Characteristics

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Junction Temperature

Figure 5: On-Resistance vs. Gate-Source Voltage

Figure 6: Body-Diode Characteristics

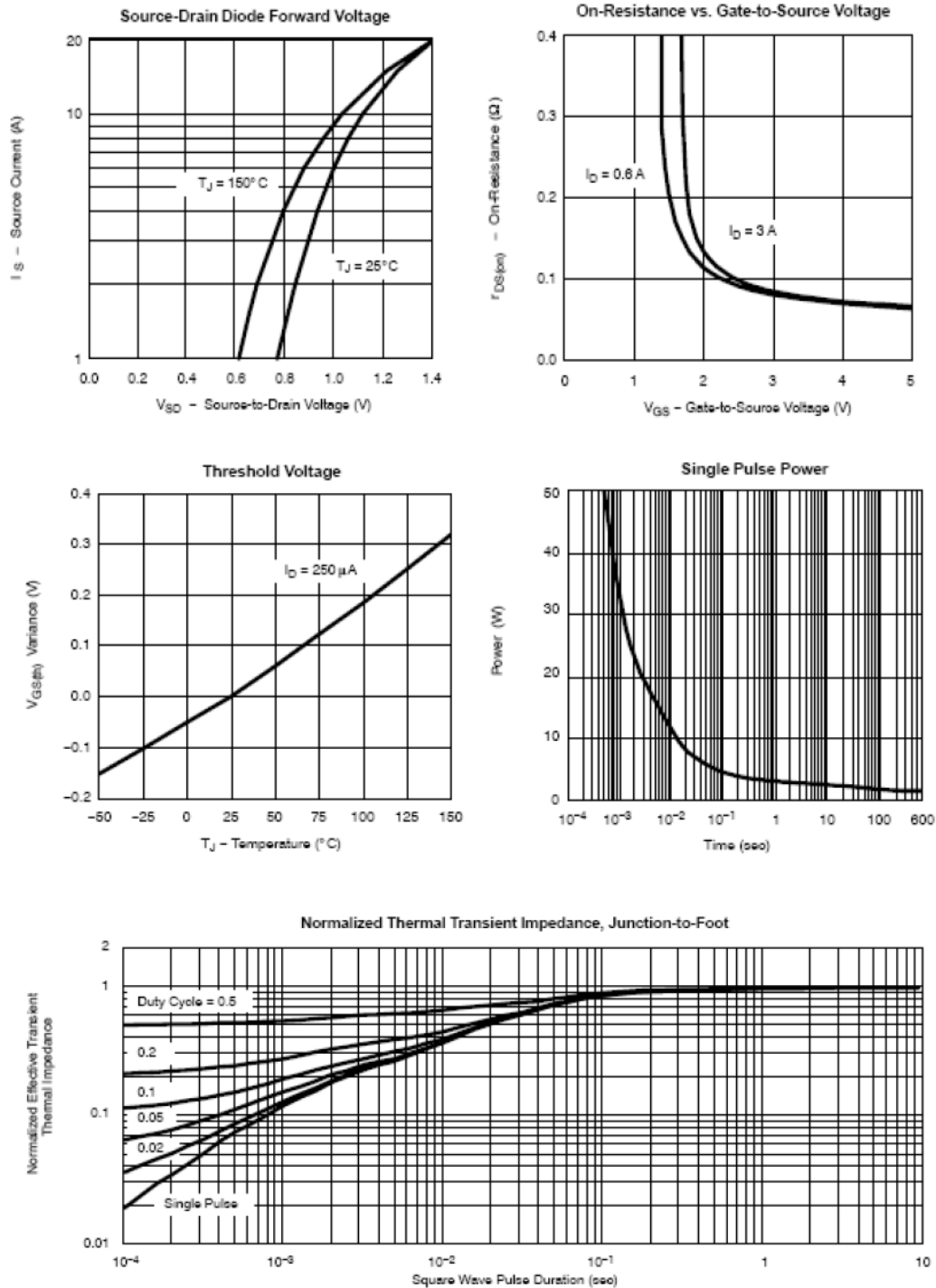


ST7407  Lead-free

P Channel Enhancement Mode MOSFET

-3.4A

TYPICAL CHARACTERISTICS (25°C Unless noted)



SOT-323 (SC-70) PACKAGE OUTLINE
